

# TPS22991 5V, 3A, 25mΩ Load Switch Device With Small Plastic Package

### 1 Features

- Integrated single channel load switch
- Input voltage range: 1V to 5.5V
- 3A maximum continuous switch current
- 25mΩ typical ON-resistance
- Low quiescent current:
  - I<sub>Q</sub> at 3.3V V<sub>IN</sub> = 6µA (typ)
- Low shutdown current:
  - I<sub>SD</sub> at 3.3V V<sub>IN</sub> = 14nA (typ)
- Controlled slew rate:
  - Version B, BN: rise time (t<sub>R</sub>) at 3.3V V<sub>IN</sub> =
  - Version C, CN: rise time (t<sub>R</sub>) at 3.3V V<sub>IN</sub> =
- Quick output discharge (QOD) of  $150\Omega$
- Thermal shutdown protection
- 0.85 × 0.75mm, 0.4mm pitch UQFN package

## 2 Applications

- PC and notebooks
- Wearables
- Solid state drive (SSD)
- **Industrial PC**

## 3 Description

The TPS22991 is a small, low  $R_{\text{ON}}$ , single channel load switch with controlled slew rate. The device contains an N-channel MOSFET that can operate over an input voltage range of 1.0V to 5.5V and can support a maximum continuous current of 3A. The switch is controlled by an on and off input, which is capable of interfacing directly with low-voltage control signals.

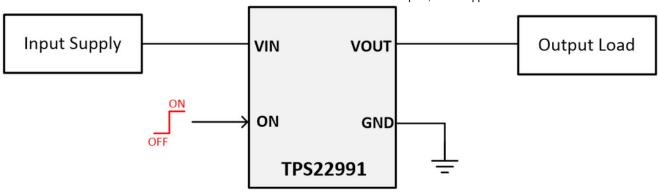
The small size and low RON makes the device ideal for being used in space constrained, battery powered applications. The wide input voltage range of the switch makes it a versatile solution for many different voltage rails. The controlled rise time of the device greatly reduces inrush current caused by large bulk load capacitances, thereby reducing or eliminating power supply droop. The TPS22991 further reduces the total solution size by integrating a 150 $\Omega$  pulldown resistor for quick output discharge (QOD) when the switch is turned off.

The TPS22991 is available in a small, space saving 0.85mm × 0.75mm, 0.4mm pitch, 4-pin UQFN package. The device is characterized for operation over the free-air temperature range of -55°C to +125°C.

## **Package Information**

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>
TPS22991	RAA (UQFN, 4)	0.85mm × 0.75mm

- For all available packages, see the orderable addendum at the end of the data sheet.
- The package size (length × width) is a nominal value and includes pins, where applicable.



**TPS22991 Typical Application** 



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# **4 Device Comparison Table**

**Table 4-1. Functionality Comparison** 

PART NUMBER	QUICK OUTPUT DISCHARGE (QOD)	TURN ON TIME
TPS22991B	Yes	Fast
TPS22991BN	No	Fast
TPS22991C	Yes	Slow
TPS22991CN	No	Slow



# **5 Pin Configuration and Functions**

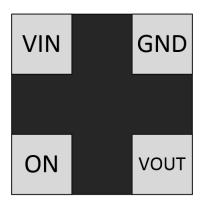


Figure 5-1. TPS22991 RAA Package, 4-Pin UQFN (Top View)

**Table 5-1. Pin Functions** 

F	PIN	I/O	DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
VIN	1	I	Switch input.
ON	2	I	Active high switch control input.
VOUT	3	0	Switch output.
GND	4	_	Device ground.

## 6 Specifications

## 6.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
V <sub>IN</sub>	Maximum input voltage range	-0.3	6	V
V <sub>OUT</sub>	Maximum output voltage range	-0.3	6	V
V <sub>ON</sub>	Maximum ON pin voltage range	-0.3	6	V
I <sub>MAX</sub>	Maximum continuous current		3	Α
I <sub>PLS</sub>	Maximum pulsed current (2ms, 2% duty cycle)		4	Α
TJ	Junction temperature	-55	150	°C
T <sub>STG</sub>	Storage temperature	-65	150	°C
T <sub>LEAD</sub>	Maximum lead temperature (10s soldering time)		300	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatio discharge	Human body model (HBM), per ANSI/ESDA/ JEDEC JS-001, all pins <sup>(1)</sup>	±1750	V
V(ESD)	V <sub>(ESD)</sub> Electrostatic discharge	Charged device model (CDM), per JEDEC specificationJESD22-C101, all pins <sup>(2)</sup>	±1000	V

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less is possible with the necessary precautions. Pins listed may actually have higher performance.

### **6.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)

		MIN	TYP MAX	UNIT
V <sub>IN</sub>	Input voltage range	1.0	5.5	V
V <sub>OUT</sub>	Output voltage range	0	5.5	V
V <sub>IH</sub>	ON pin high voltage Range	0.8	5.5	V
V <sub>IL</sub>	ON pin low voltage range	0	0.35	V
T <sub>A</sub>	Ambient temperature	<b>–</b> 55	125	°C

### 6.4 Thermal Information

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		TPS22991	
	THERMAL METRIC(1)	4 PINS	UNIT
		RAA	
R <sub>0JA</sub>	Junction-to-ambient thermal resistance	225.3	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	214.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	83.6	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	13.1	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	83	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



## **6.5 Electrical Characteristics**

Typical values at VIN = 3.3V unless otherwise specified

,,	alues at VIN = 3.3V unless otherwise s PARAMETER		ONDITIONS	T <sub>A</sub>	MIN TYP	MAX	UNIT
INPUT SU	IPPLY (VIN)						
				25°C	6		μA
I <sub>Q, VIN</sub>	VIN quiescent current	V <sub>ON</sub> ≥ V <sub>IH</sub> , VOUT :	= Open	-40°C to 85°C		12	
α, τπτ	·		•	–55°C to 125°C		14	
				25°C	14		nA
I <sub>SD, VIN</sub>	VIN shutdown current	V <sub>ON</sub> ≤ V <sub>IL</sub> , VOUT =	= Open	-40°C to 85°C		20	μA
02, 1			·	–55°C to 125°C		67	
				25°C	15		nA
I <sub>SD, VIN</sub>	VIN shutdown current	V <sub>ON</sub> ≤ V <sub>IL</sub> , VOUT = GND	V <sub>ON</sub> ≤ V <sub>IL</sub> , VOUT = GND	–40°C to 85°C		20	μA
,		- GND	- GND	–55°C to 125°C		67	μΑ
ON-RESIS	STANCE (RON)						
				25°C	25		mΩ
				–40°C to 85°C		35	mΩ
			V <sub>IN</sub> = 5V	-40°C to 105°C		38	mΩ
				–55°C to 125°C		40	mΩ
				25°C	25		mΩ
				–40°C to 85°C		35	mΩ
			V <sub>IN</sub> = 3.3V	–40°C to 105°C		38	mΩ
_				–55°C to 125°C		40	mΩ
R <sub>ON</sub>	ON-state resistance	I <sub>OUT</sub> = -200mA		25°C	25		mΩ
			1 0 1	-40°C to 85°C		35	mΩ
			V <sub>IN</sub> = 1.8V	-40°C to 105°C		38	mΩ
				–55°C to 125°C		40	mΩ
				25°C	35		mΩ
			\/ - 4\/	–40°C to 85°C		48	mΩ
			V <sub>IN</sub> = 1V	-40°C to 105°C		52	mΩ
				–55°C to 125°C		60	mΩ
THERMAI	L SHUTDOWN (TSD)						
T <sub>SD,R</sub>	Thermal shutdown			Rising	170		°C
T <sub>SD,F</sub>	Thermal shutdown			Falling	150		°C
ENABLE	PIN (ON)						
I <sub>ON</sub>	ON pin leakage	V <sub>ON</sub> ≥ V <sub>IH</sub>		–55°C to 125°C		100	nA
R <sub>PD, ON</sub>	Smart pull down resistance	$V_{ON} \le V_{IL}$		–55°C to 125°C	500		kΩ
$V_{IH,ON}$	ON pin threshold (VIH rising)			–55°C to 125°C		0.8	V
$V_{Hys,ON}$	ON pin threshold (hysteresis)			–55°C to 125°C	0.07		V
$V_{IL,ON}$	ON pin threshold (VIL falling)			–55°C to 125°C	0.35		V
QUICK O	UTPUT DISCHARGE (QOD)						
	OOD win internal III.		V <sub>IN</sub> = 1V	–55°C to 125°C	190		Ω
$R_{QOD}$	QOD pin internal discharge resistance (Version B, C)	$V_{ON} \le V_{IL}$	V <sub>IN</sub> = 3.3V	–55°C to 125°C	25 25 25 25 35 170 150 500 0.07		Ω
			V <sub>IN</sub> = 5V	–55°C to 125°C	140		Ω

## 6.6 Switching Characteristics (Version C, CN)

Unless otherwise noted, the typical characteristics in the following table apply to an input voltage of 3.3V, an ambient temperature of 25°C, and a load of  $CL = 0.1 \mu F$ ,  $RL = 10 \Omega$ . Timing parameter measurement details are shown in the timing diagram in the data sheet. Parameter not tested in production

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
		VIN = 5.0V		1119		μs
ON Turn ON time    VIN = 5.0V     VIN = 3.3V     VIN = 1.8V     VIN = 5.0V     VIN = 5.0V     VIN = 3.3V     VIN = 1.8V     VIN = 1.8V     VIN = 1.0V     VIN = 3.3V     VIN = 3.3V     VIN = 1.8V     VIN = 1.0V     VIN = 5.0V     VIN = 5.0V     VIN = 5.0V     VIN = 1.8V     VIN = 1.0V     VIN = 5.0V     VIN = 5.0V     VIN = 5.0V     VIN = 5.0V     VIN = 3.3V     VIN = 5.0V     VIN = 3.3V     VI	VIN = 3.3V		996		μs	
ON	Turn ON time	VIN = 1.8V		853		μs
		VIN = 1.0V		774		μs
		VIN = 5.0V		794		μs
•	Output rice time	VIN = 3.3V		662		μs
<sup>L</sup> R	Output rise time	VIN = 1.8V		514		μs
		VIN = 1.0V		397		μs
		VIN = 5.0V		332		μs
	Dolay time	VIN = 3.3V		341		μs
ιD	Delay une	VIN = 1.8V		346		μs
		VIN = 1.0V		383		μs
		VIN = 5.0V		6		μs
	Turn OFF time	VIN = 3.3V		4		μs
OFF	Turn OFF time	VIN = 1.8V		2		μs
		VIN = 1.0V		4		μs
		VIN = 5.0V		5		μs
	Output Fall time	VIN = 3.3V		5		μs
t <sub>F</sub>	Output Fall time	VIN = 1.8V		5		μs
		VIN = 1.0V		5		μs

## 6.7 Switching Characteristics (Version B, BN)

Unless otherwise noted, the typical characteristics in the following table apply to an input voltage of 3.3V, an ambient temperature of  $25^{\circ}$ C, and a load of CL =  $0.1\mu$ F, RL =  $10\Omega$ . Timing parameter measurement details are shown in the timing diagram in the data sheet. Parameter not tested in production

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
		VIN = 5.0V		302		μs
	Turn ON time	VIN = 3.3V		259		μs
t <sub>ON</sub>	Turn ON time	VIN = 1.8V		216		μs
		VIN = 1.0V		198		μs
		VIN = 5.0V		173		μs
	Output rice time	VIN = 3.3V		141	73 41 27	μs
t <sub>R</sub>	Output rise time	VIN = 1.8V		107 81 127	μs	
		VIN = 1.0V		81		μs
		VIN = 5.0V		127		μs
	Dolov timo	VIN = 3.3V		117		μs
$t_D$	Delay time	VIN = 1.8V		109		μs
		VIN = 1.0V		116		μs
		VIN = 5.0V		6		μs
t	Turn OFF time	VIN = 3.3V		4		μs
t <sub>OFF</sub>	Tum OFF time	VIN = 1.8V		2		μs
		VIN = 1.0V		4	MAX	μs

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# 6.7 Switching Characteristics (Version B, BN) (continued)

Unless otherwise noted, the typical characteristics in the following table apply to an input voltage of 3.3V, an ambient temperature of  $25^{\circ}$ C, and a load of CL =  $0.1\mu$ F, RL =  $10\Omega$ . Timing parameter measurement details are shown in the timing diagram in the data sheet. Parameter not tested in production

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t Output fall time		VIN = 5.0V		5		μs
	Output fall time	VIN = 3.3V		5		μs
\F	Output fall time	VIN = 1.8V		5		μs
		VIN = 1.0V		5		μs



## 7 Typical Characteristics

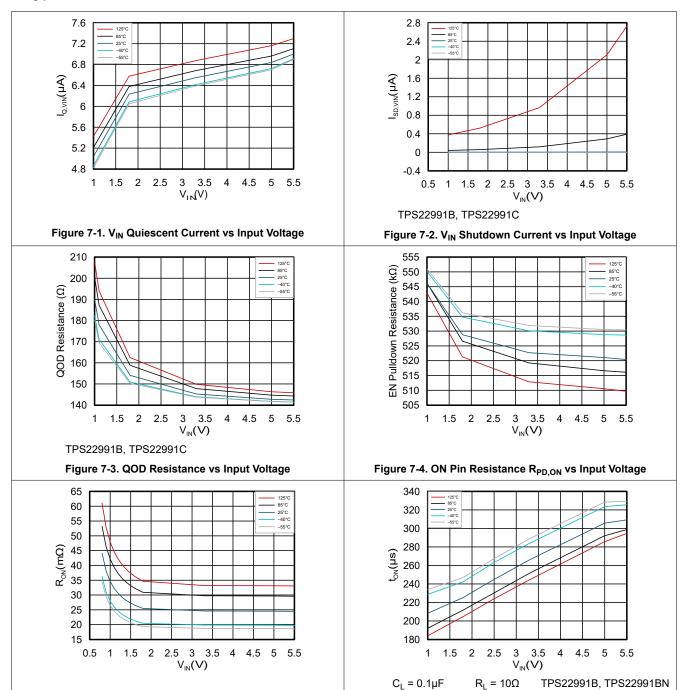
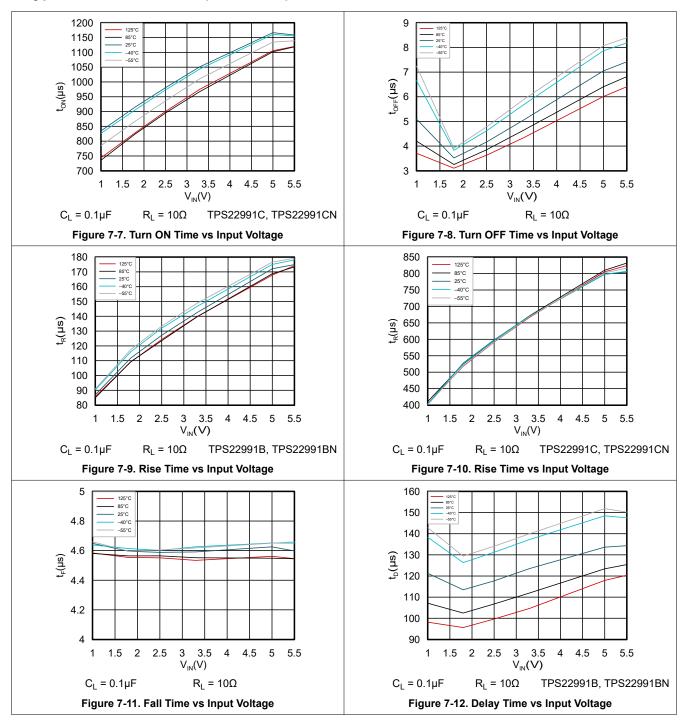


Figure 7-5. R<sub>ON</sub> vs Input Voltage

Figure 7-6. Turn ON Time vs Input Voltage



# 7 Typical Characteristics (continued)

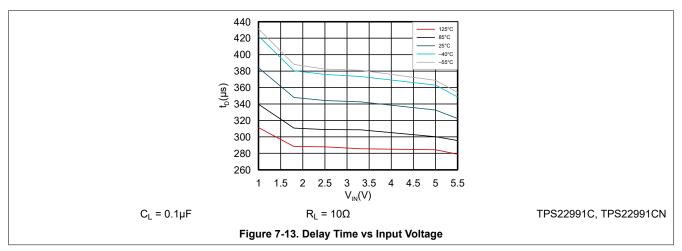


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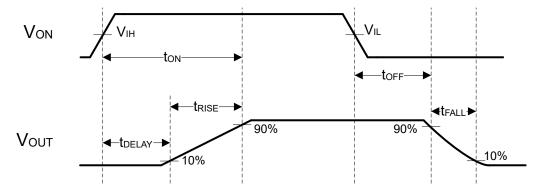


# 7 Typical Characteristics (continued)





# **8 Parameter Measurement Information**



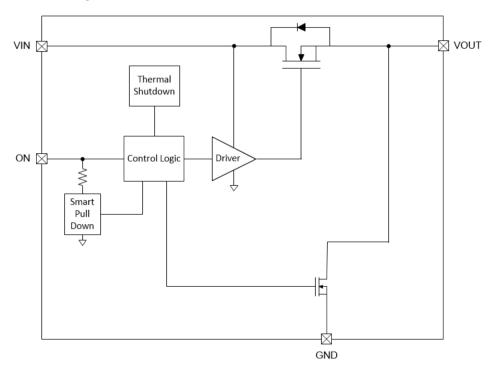
**Figure 8-1. Timing Parameter Measurement Information** 

## 9 Detailed Description

### 9.1 Overview

The TPS22991 is a small, low  $R_{ON}$ , single channel load switch with controlled slew rate. The device contains an N-channel MOSFET that can operate over an input voltage range of 1V to 5.5V and can support a maximum continuous current of 3A. The switch is controlled by an on and off input, which is capable of interfacing directly with low-voltage control signals.

## 9.2 Functional Block Diagram



### 9.3 Feature Description

### 9.3.1 On and Off Control

The ON pin controls the state of the switch. The ON pin is compatible with standard GPIO logic threshold so it can be used in a wide variety of applications. When power is first applied to  $V_{IN}$ , a smart pulldown is used to keep the ON pin from floating until the system sequencing is complete. After the ON pin is deliberately driven high ( $\geq V_{IH}$ ), the smart pulldown is disconnected to prevent unnecessary power loss. See Table 9-1 when the ON pin smart pulldown is active.

Table 9-1. On Pin Control

ON PIN VOLTAGE	ON PIN SMART PULLDOWN STATUS		
≤ V <sub>IL</sub>	Smart pulldown resistance active		
≥ V <sub>IH</sub>	Smart pulldown disconnected		

#### 9.3.2 Quick Output Discharge

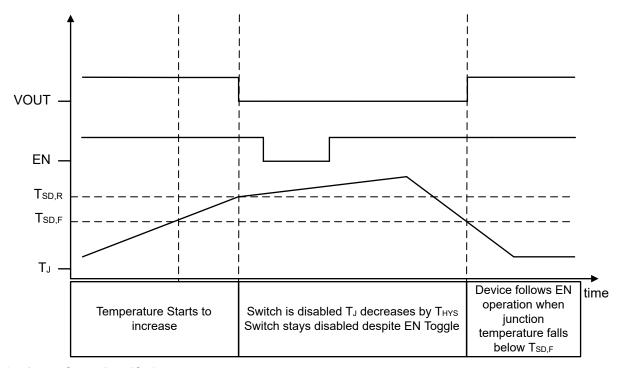
TPS22991B and TPS22991C integrates quick output discharge. When the switch is disabled, a discharge resistor is connected between VOUT and GND. This resistor has a typical value of  $150\Omega$  when  $V_{IN}$  = 3.3V, and prevents the output from floating while the switch is disabled.

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#### 9.3.3 Thermal Shutdown

When the device temperature reaches T<sub>SD, R</sub>, the device shuts itself off to prevent thermal damage. After the device cools off to T<sub>SD.F</sub>, it turns back on. If the device is kept in a thermally stressful environment, then the device oscillates between these two states until it can keep its temperature below the thermal shutdown point.



### 9.3.4 Input Capacitor (C<sub>IN</sub>)

To limit the voltage drop on the input supply caused by transient in-rush currents when the switch turns on into a discharged load capacitor or short-circuit, a capacitor needs to be placed between VIN and GND. A 1µF ceramic capacitor, CIN, placed close to the pins, is usually sufficient. Higher values of CIN can be used to further reduce the voltage drop during high-current application. When switching heavy loads, it is recommended to have an input capacitor about 10 times higher than the output capacitor to avoid excessive voltage drop.

## 9.3.5 Output Capacitor (C<sub>L</sub>)

Due to the integrated body diode in the MOSFET, a C<sub>IN</sub> greater than C<sub>L</sub> is highly recommended. A C<sub>L</sub> greater than CIN can cause VOUT to exceed VIN when the system supply is removed. This could result in current flow through the body diode from  $V_{OUT}$  to  $V_{IN}$ . A  $C_{IN}$  to  $C_L$  ratio of 10 to 1 is recommended for minimizing  $V_{IN}$  dip caused by inrush currents during startup.

#### 9.4 Device Functional Modes

The table below describes the connection of the VOUT pin depending on the state of the ON pin.

ON	FAULT CONDITION	VOUT STATE		
L	N/A	<ul><li>Hi-Z for BN, CN</li><li>GND through QOD resistor for B, C</li></ul>		
Н	None	V <sub>IN</sub> through R <sub>ON</sub>		
X	Thermal shutdown	<ul><li>Hi-Z for BN, CN</li><li>GND through QOD resistor for B, C</li></ul>		

## 10 Application and Implementation

### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

## 10.1 Application Information

The input to output voltage drop in the device is determined by the  $R_{ON}$  of the device and the load current. The  $R_{ON}$  of the device depends upon the  $V_{IN}$  condition of the device. After the  $R_{ON}$  of the device is determined based upon the  $V_{IN}$  condition, use the below equation to calculate the input to output voltage drop.

$$\Delta V = I_{LOAD} \times R_{ON} \tag{1}$$

#### where

- ΔV is the voltage drop from V<sub>IN</sub> to V<sub>OUT</sub>.
- I<sub>LOAD</sub> is the load current.
- R<sub>ON</sub> is the on-resistance of the device for a specific VIN and VBIAS.

## 10.2 Typical Application

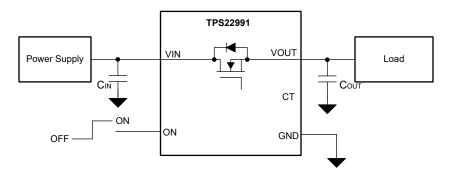


Figure 10-1. Typical Application Diagram

**Table 10-1. Recommended External Components** 

COMPONENT	TYPICAL VALUE	PURPOSE					
C <sub>IN</sub>	1µF	Filtering voltage transients					
C <sub>OUT</sub>	100nF	Filtering voltage transients					

### 10.2.1 Design Requirements

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For this design example, use the input parameters shown in Table 10-2.

**Table 10-2. Design Parameters** 

DESIGN PARAMETER	EXAMPLE VALUE
V <sub>IN</sub>	5V
Load current	2A
Load capacitance	10μF



## 10.2.2 Detailed Design Procedure

The input to output voltage drop in the device is determined by the  $R_{ON}$  of the device and the load current. The  $R_{ON}$  of the device depends upon the  $V_{IN}$  condition of the device. After the  $R_{ON}$  of the device is determined based upon the  $V_{IN}$  condition, use the below equation to calculate the input to output voltage drop.

$$\Delta V = I_{LOAD} \times R_{ON} \tag{2}$$

#### where

- ΔV is the voltage drop from V<sub>IN</sub> to V<sub>OUT</sub>.
- I<sub>LOAD</sub> is the load current.
- R<sub>ON</sub> is the on-resistance of the device for a specific VIN and VBIAS.

An appropriate I<sub>LOAD</sub> must be chosen such that the I<sub>MAX</sub> specification of the device is not violated.

To determine how much inrush current is caused by the load capacitance, use Equation 3.

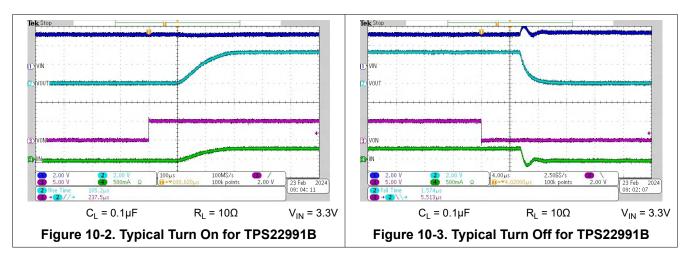
$$I_{INRUSH} = C_L \times dV_{OUT} / dt$$
 (3)

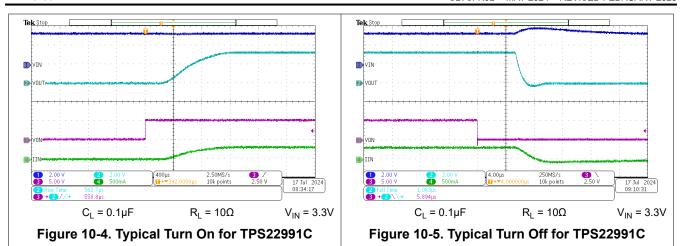
#### where

- I<sub>INRUSH</sub> is amount of inrush current caused by C<sub>L</sub>
- C<sub>L</sub> is the load capacitance on V<sub>OUT</sub>
- dt is the rise time for V<sub>OUT</sub> when the device is enabled
- dV<sub>OUT</sub> is change in the V<sub>OUT</sub> voltage after the device is enabled.

The slew rate of the device  $dV_{OUT}/dt$  at a given  $V_{IN}$  voltage can be found in the electrical characteristic table for a given version.  $I_{INRUSH}$  has to be within the  $I_{MAX}$  and  $I_{PLS}$  limits.

## 10.2.3 Application Curves





## 10.3 Power Supply Recommendations

The TPS22991 device is designed to operate with a  $V_{IN}$  range of 1V to 5.5V. Regulate the  $V_{IN}$  power supply well and place as close to the device terminal as possible. The power supply must be able to withstand all transient load current steps. In most situations, using an input capacitance ( $C_{IN}$ ) of 1 $\mu$ F is sufficient to prevent the supply voltage from dipping when the switch is turned on. In cases where the power supply is slow to respond to a large transient current or large load current step, additional bulk capacitance can be required on the input.

## 10.4 Layout

## 10.4.1 Layout Guidelines

For best performance, all traces must be as short as possible. To be most effective, place the input and output capacitors close to the device to minimize the effects that parasitic trace inductances can have on normal operation. Using wide traces for VIN, VOUT, and GND helps minimize the parasitic electrical effects.

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## 10.4.2 Layout Example

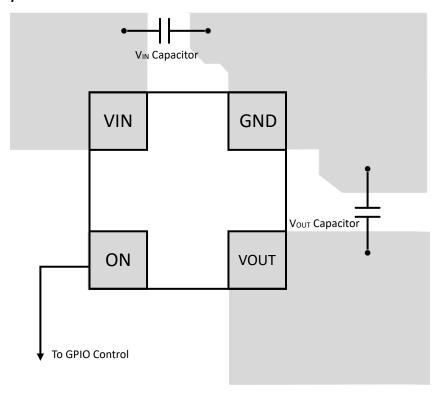


Figure 10-6. TPS22991 Layout

## 11 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### 11.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

## 11.2 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

### 11.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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### 11.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## 11.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

## **12 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (August 2024) to Revision B (February 2024)					
Deleted the notes for device preview	3				

## Changes from Revision \* (May 2024) to Revision A (August 2024)

Page



# 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 23-May-2025

### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
PTPS22991BRAAR	Active	Preproduction	UQFN-HR (RAA)   4	3000   LARGE T&R	-	Call TI	Call TI	-55 to 125	
PTPS22991BRAAR.A	Active	Preproduction	UQFN-HR (RAA)   4	3000   LARGE T&R	-	Call TI	Call TI	-55 to 125	
TPS22991BRAAR	Active	Production	UQFN-HR (RAA)   4	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-55 to 125	Н
TPS22991BRAAR.A	Active	Production	UQFN-HR (RAA)   4	3000   LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-55 to 125	Н

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

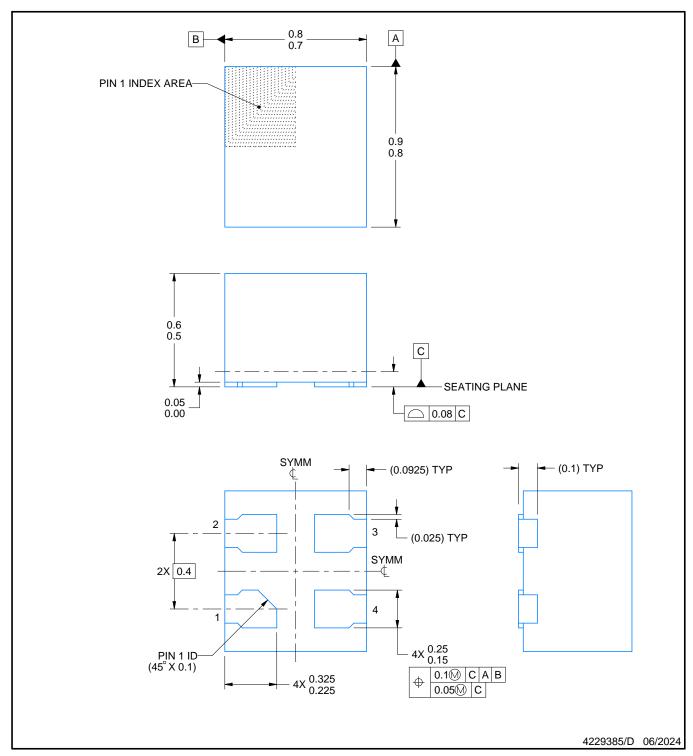
<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PLASTIC QUAD FLATPACK - NO LEAD

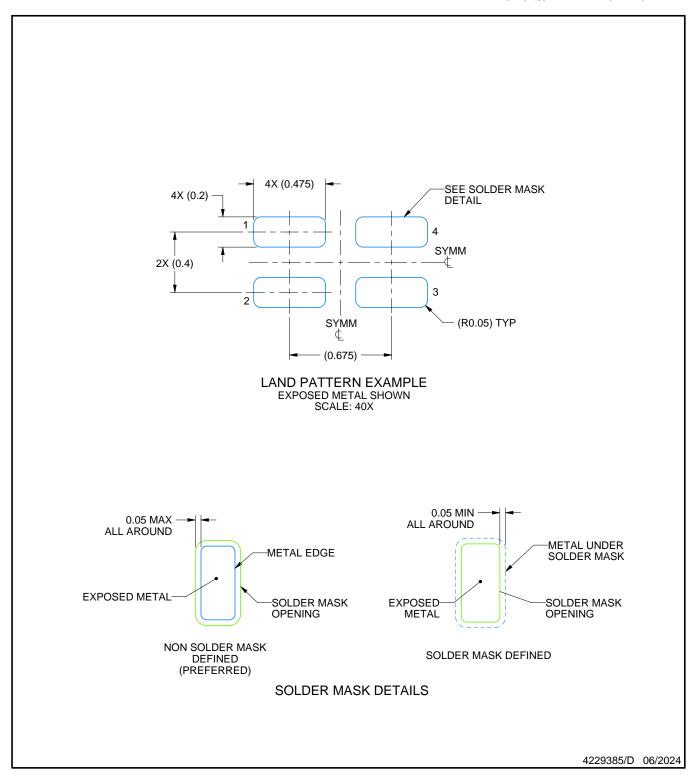


### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

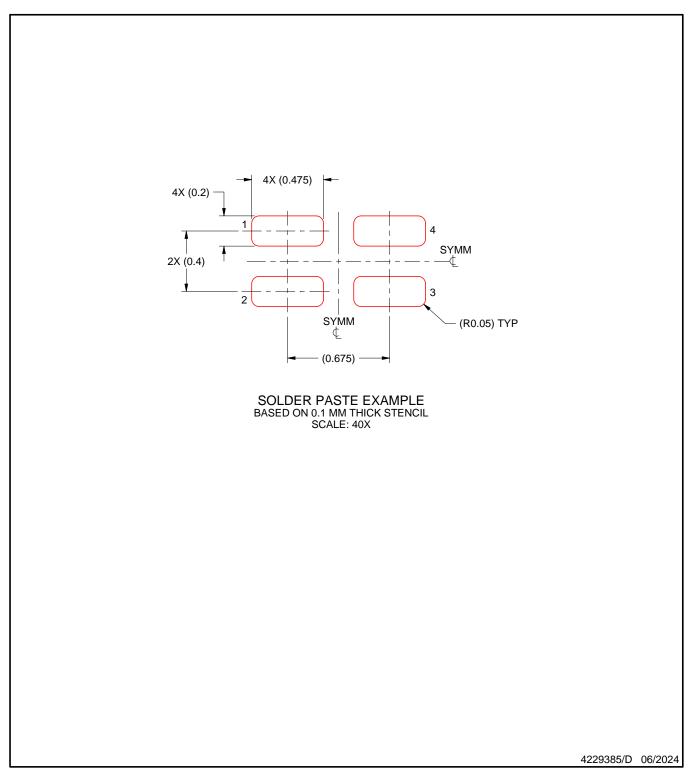


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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